MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

5.0SMDJ11(C)A - 5.0SMDJ170(C)A

Product specification





Features

- For surface mounted applications in order to optimize board space
- Low profile package
- Built-in strain relief
- Glass passivated junction
- Low inductance
- Excellent clamping capability
- 5000W peak pulse power capability at 10/1000µswaveform, repetition rate (duty cycle): 0.01%
- Fast response time
- Typical IR less than 2µA above 22V
- High Temperature soldering: 260°C/10 seconds at terminals
- Plastic package has underwriters laboratory flammability 94V-0
- Meets MSL level 1, per J-STD-020
- Safety certification: UL: E244458

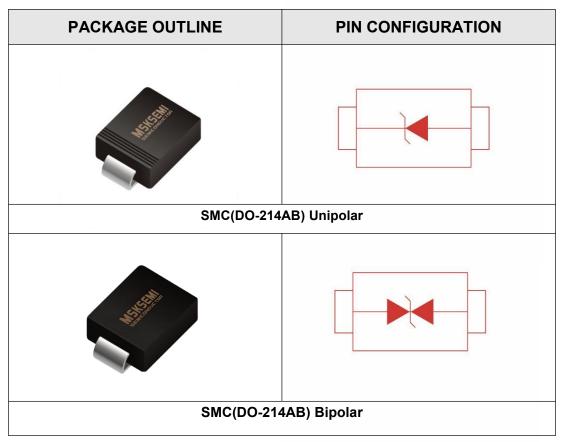
Mechanical Data

- Case: JEDEC DO-214AB. Molded plastic over glass passivated junction
- Terminal: Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode except bi-directional models
- Standard Packaging: 16mm tape (EIA STD RS-481)
- Weight: 0.30g

Applications

- I/O interface
- AC/DC power supply
- Low frequency signal transmission line (RS232, RS485, etc.)

Reference News





Ratings at 25°C ambient temperature unless otherwise specified.

Rating	Symbol	Value	Units
Peak pulse power dissipation at 10/1000µs waveform (Note1, Note2, Fig.1)	Р _{РРМ}	Minimum 5000	Watts
Peak pulse current of at 10/1000µs waveform (Note 1, Fig.3)	I _{PPM}	See Table	Amps
Steady state power dissipation at T_A=50 $^\circ\!\mathrm{C}$ (Fig.5)	P _{M(AV)}	6.5	Watts
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load, (JEDEC Method) (Note3, Fig.6)	I _{FSM}	300	Amps
Operating junction and Storage Temperature Range.	T _J ,T _{STG}	-55 to +150	°C
Typical thermal resistance junction to lead	R _{eJL}	15	°C /W
Typical thermal resistance junction to ambient	R _{0JA}	75	°C/W

Notes: 1. Non-repetitive current pulse, per Fig.3 and derated above $T_A=25^{\circ}C$ per Fig.2.

- 2. Mounted on 8.0mm×8.0mm copper pads to each terminal.
- 3. 8.3ms single half sine-wave, or equivalent square wave, duty cycle=4 pulses per minutes maximum.

Electrical Characteristics (TA=25℃)

Part Nu	umber	Mar	vice king ode	Reverse Stand-Off Voltage	Breakdown Voltage @h	Test Current	Maximum Clamping Voltage @I _{PP}	Peak Pulse Current	Reverse Leakage @V _{RWM}
Unidirectional	Bidirectional	UNI	BI	V _{RWM} (V)	V _{BR} (V)	ե(mA)	Vc(V)	IPP(A)	l _R (μA)
5.0SMDJ11A	5.0SMDJ11CA	5PEN	5BEN	11.0	12.20~13.50	10	18.2	275.00	800
5.0SMDJ12A	5.0SMDJ12CA	5PEP	5BEP	12.0	13.30~14.70	10	19.9	252.00	800
5.0SMDJ13A	5.0SMDJ13CA	5PEQ	5BEQ	13.0	14.40~15.90	10	21.5	233.00	500
5.0SMDJ14A	5.0SMDJ14CA	5PER	5BER	14.0	15.60~17.20	10	23.2	216.00	200
5.0SMDJ15A	5.0SMDJ15CA	5PES	5BES	15.0	16.70~18.50	1	24.4	205.00	100
5.0SMDJ16A	5.0SMDJ16CA	5PET	5BET	16.0	17.80~19.70	1	26.0	193.00	50
5.0SMDJ17A	5.0SMDJ17CA	5PEU	5BEU	17.0	18.90~20.90	1	27.6	181.00	20
5.0SMDJ18A	5.0SMDJ18CA	5PEV	5BEV	18.0	20.00~22.10	1	29.2	172.00	10
5.0SMDJ20A	5.0SMDJ20CA	5PEW	5BEW	20.0	22.20~24.50	1	32.4	155.00	5
5.0SMDJ22A	5.0SMDJ22CA	5PEX	5BEX	22.0	24.40~26.90	1	35.5	141.00	5
5.0SMDJ24A	5.0SMDJ24CA	5PEZ	5BEZ	24.0	26.70~29.50	1	38.9	129.00	2
5.0SMDJ26A	5.0SMDJ26CA	5PFE	5BFE	26.0	28.90~31.90	1	42.1	119.00	2
5.0SMDJ28A	5.0SMDJ28CA	5PFG	5BFG	28.0	31.10~34.40	1	45.4	110.00	2
5.0SMDJ30A	5.0SMDJ30CA	5PFK	5BFK	30.0	33.30~36.80	1	48.4	103.00	2

MSKSEMI SEMICONDUCTOR

5.0SMDJ11(C)A - 5.0SMDJ170(C)A

Part N	umber	Mar	vice king ode	Reverse Stand-Off Voltage	Breakdown Voltage @I r	Test Current	Maximum Clamping Voltage @I _{PP}	Peak Pulse Current	Reverse Leakage @Vrwm
Unidirectional	Bidirectional	UNI	BI	V _{RWM} (V)	V _{BR} (V)	ե(mA)	V _c (V)	I _{PP} (A)	l _R (μA)
5.0SMDJ33A	5.0SMDJ33CA	5PFM	5BFM	33.0	36.70~40.60	1	53.3	93.90	2
5.0SMDJ36A	5.0SMDJ36CA	5PFP	5BFP	36.0	40.00~44.20	1	58.1	86.10	2
5.0SMDJ40A	5.0SMDJ40CA	5PFR	5BFR	40.0	44.40~49.10	1	64.5	77.60	2
5.0SMDJ43A	5.0SMDJ43CA	5PFT	5BFT	43.0	47.80~52.80	1	69.4	72.10	2
5.0SMDJ45A	5.0SMDJ45CA	5PFV	5BFV	45.0	50.00~55.30	1	72.7	68.80	2
5.0SMDJ48A	5.0SMDJ48CA	5PFX	5BFX	48.0	53.30~58.90	1	77.4	64.70	2
5.0SMDJ51A	5.0SMDJ51CA	5PFZ	5BFZ	51.0	56.70~62.70	1	82.4	60.70	2
5.0SMDJ54A	5.0SMDJ54CA	5PGE	5BGE	54.0	60.00~66.30	1	87.1	57.50	2
5.0SMDJ58A	5.0SMDJ58CA	5PGG	5BGG	58.0	64.40~71.20	1	93.6	53.50	2
5.0SMDJ60A	5.0SMDJ60CA	5PGK	5BGK	60.0	66.70~73.70	1	96.8	51.70	2
5.0SMDJ64A	5.0SMDJ64CA	5PGM	5BGM	64.0	71.10~78.60	1	103.0	48.60	2
5.0SMDJ70A	5.0SMDJ70CA	5PGP	5BGP	70.0	77.80~86.00	1	113.0	44.30	2
5.0SMDJ75A	5.0SMDJ75CA	5PGR	5BGR	75.0	83.30~92.10	1	121.0	41.40	2
5.0SMDJ78A	5.0SMDJ78CA	5PGT	5BGT	78.0	86.70~95.80	1	126.0	39.70	2
5.0SMDJ85A	5.0SMDJ85CA	5PGV	5BGV	85.0	94.40~104.00	1	137.0	36.50	2
5.0SMDJ90A	5.0SMDJ90CA	5PGX	5BGX	90.0	100.00~111.00	1	146.0	34.30	2
5.0SMDJ100A	5.0SMDJ100CA	5PGZ	5BGZ	100.0	111.00~123.00	1	162.0	30.90	2
5.0SMDJ110A	5.0SMDJ110CA	5PHE	5BHE	110.0	122.00~135.00	1	177.0	28.30	2
5.0SMDJ120A	5.0SMDJ120CA	5PHG	5BHG	120.0	133.00~147.00	1	193.0	26.00	2
5.0SMDJ130A	5.0SMDJ130CA	5PHK	5BHK	130.0	144.00~159.00	1	209.0	24.00	2
5.0SMDJ150A	5.0SMDJ150CA	5PHM	5BHM	150.0	167.00~185.00	1	243.0	20.60	2
5.0SMDJ160A	5.0SMDJ160CA	5PHP	5BHP	160.0	178.00~197.00	1	259.0	19.30	2
5.0SMDJ170A	5.0SMDJ170CA	5PHR	5BHR	170.0	189.00~209.00	1	275.0	18.20	2

Notes: For bidirectional type having $V_{\text{RWM}}\,$ of 18V and less, the I_{R} limit is double.



Ratings and Characteristic Curves (TA=25℃ unless otherwise noted)

Figure 1. Peak Pulse Power Rating Curve

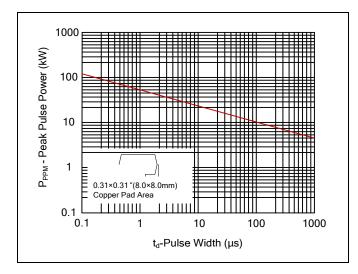
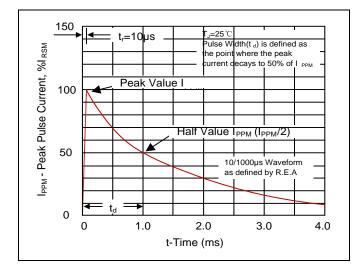
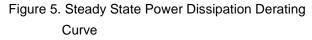


Figure 3. Pulse Waveform





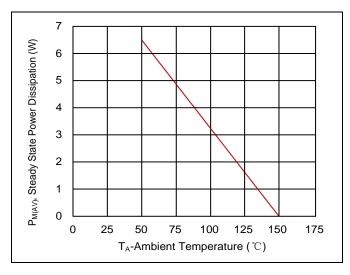


Figure 2. Pulse Derating Curve

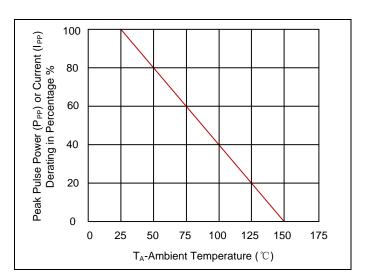


Figure 4. Typical Junction Capacitance

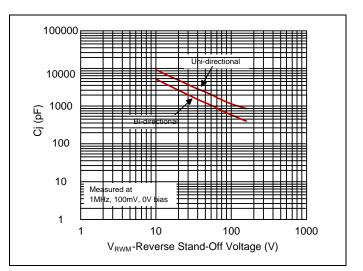
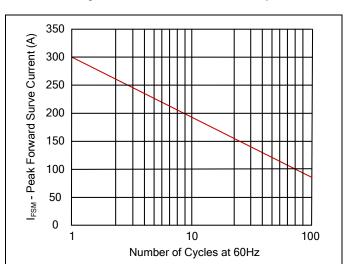
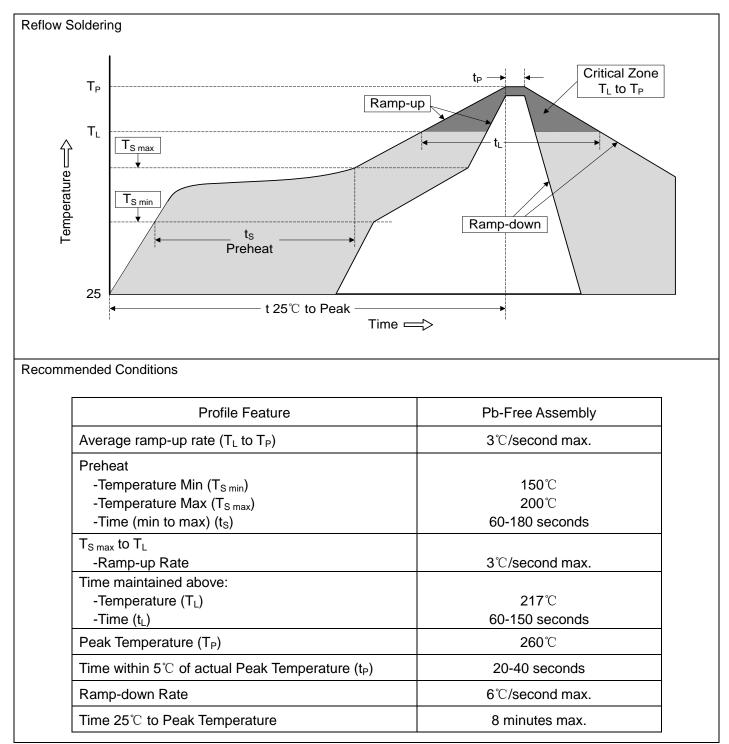


Figure 6. Maximum Non-Repetitive Forward Surge Current Uni-Directional Only





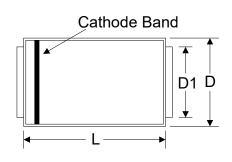
Recommended Soldering Conditions

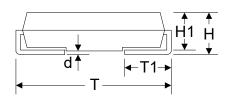




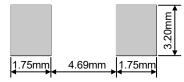
Dimensions (SMC/DO-214AB)

Product:





Pad:



Symbol	Millim	neters	Inches		
Symbol	Min.	Max.	Min.	Max.	
L	6.60	7.11	0.	0.	
D	5.59	6.22	2600.	2800.	
D1	2.90	3.20	2200.	2450.	
Т	7.75	8.13	1140.	1260.	
T1	0.76	1.52	3050.	3200.	
d	-	0.203	030	0600.	
н	2.20	2.80	0.087	0080.	
H1	2.06	2.62	0.079	0.103	

REELSPECIFICATION

P/N	PKG	QTY
5.0SMDJ11(C)A - 5.0SMDJ170(C)A	SMC	3000



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